IGBT (Insulated Gate Bipolar Transistor)

Features:

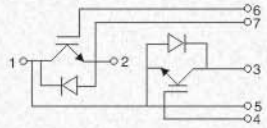
- SPT chip (Soft-punch-through technology)
- MOS input control
- Ultra thin IGBT chip, great current, low loss, low tail current
- Low $V_{CE(SAT)}$ with positive temperature coefficient
- High switch frequency, low switch loss
- High SC resistive ability
- Optimum EMC property
- Long creepage distance
- DBC insulated voltage =2,500V RMS
- 'Vacuum +H_2' process gas atmosphere, nearly voidless soldering results
- Ultrasonic scan technique, assure soldering quality

Applications:

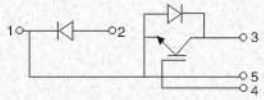
- AC and DC electric motor control
- Frequency transformer
- UPS
- Industrial power supply
- Electric welding machine

Series SGG50/75/100/150/200/300

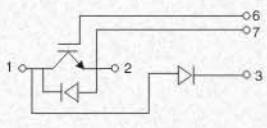
Type	IGBT						Diode				Outline
	I_C @T_C= 80℃ A	V_{CES} V	V_{GES} V	$V_{GE(TH)}$ V	V_{ISO} V	T_{vj} ℃	I_F @T_C= 80℃ A	I_{FRM} @T_C= 80℃ A	I_{FSM} @T_C= 125℃ A	trr ns	
SGG50-12CS1	50	1200	±20	4.5-7.5	2500	150	50	100	500	400	WI-1
SGG50-12RS1											
SGG50-12LS1											
SGG75-12CS1	75	1200	±20	4.5-7.5	2500	150	75	150	700	200	WI-1
SGG75-12RS1											
SGG75-12LS1											
SGG100-12CS1	100	1200	±20	4.5-7.5	2500	150	95	190	1000	200	WI-1
SGG100-12RS1											
SGG100-12LS1											
SGG150-12CS2	150	1200	±20	4.5-7.5	2500	150	150	300	1400	200	WI-2
SGG150-12RS2											
SGG150-12LS2											
SGG200-12CS2	200	1200	±20	4.5-7.5	2500	150	200	400	1800	200	WI-2
SGG200-12RS2											
SGG200-12LS2											
SGG300-12CS2	300	1200	±20	4.5-7.5	2500	150	300	600	2200	220	W I-2
SGG300-12RS2											
SGG300-12LS2											



SGG50/75/100-12CS1
SGG150/200/300-12CS2



SGG50/75/100-12RS1
SGG150/200/300-12RS2



SGG50/75/100-12LS1
SGG150/200/300-12LS2